

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2824
	Examiner Name	Unknown HIEN NGUYEN
Sheet 1 of 1		Attorney Docket No: 303.620US2

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
HN	US-4,051,354	09/27/1977	Choate, W. C.	235	312	07/03/1975
HN	US-5,324,681	06/28/1994	Lowrey, T. A., et al.	437	52	02/22/1993
HN	US-5,327,380	07/05/1994	Kersh III, D. V., et al.	365	195	02/08/1991
HN	US-5,493,141	02/20/1996	Ricco, B., et al.	257	321	04/21/1994
HN	US-5,764,096	06/09/1998	Lipp, R. J., et al.	327	434	11/21/1996
HN	US-5,768,192	06/16/1998	Eitan, Boaz	365	185.24	07/23/1996
HN	US-5,781,477	07/14/1998	Rinerson, D.D., et al.	365	185.29	02/23/1996
HN	US-6,038,168	03/14/2000	Allen, A. J., et al.	365	185.07	06/26/1998
HN	US-6,229,733	05/08/2001	Male, B.	365	185.18	12/30/1999

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ⁴
HN		EITAN, BOAZ, "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell", <u>IEEE Electron Device Letters</u> , 21(11), (November 2000), 543-545		
HN		FISCHETTI, M. V., et al., "The effect of gate metal and SiO ₂ thickness on the generation of donor states at the Si-SiO ₂ interface", <u>Journal of Applied Physics</u> , vol. 57, no. 2, (January 1985), 418-424		
HN		LUSKY, ELI, et al., "Spatial characterization of Channel hot electron injection Utilizing subthreshold slope of NROM memory device", pp. 1-2		
HN		NING, T. H., "Capture cross section and trap concentration of holes in silicon dioxide", <u>Journal of Applied Physics</u> , vol. 47, no. 3, (March 1976), 1079-1081		
HN		NING, T. H., et al., "Completely electrically reprogrammable nonvolatile memory device using conventional p-channel MOSFET", <u>IBM Technical Disclosure Bulletin</u> , vol. 20, no. 5, (October 1977), 2016		
HN		NING, T. H., et al., "Erasable nonvolatile memory device using hole trapping in SiO ₂ ", <u>IBM Technical Disclosure Bulletin</u> , vol. 18, no. 8, (January 1976), 2740-2742		
HN		ROIZIN, YAKOV, et al., "'Dummy' GOX for Optimization of microFLASH Technology", 2 pages		
HN		ROIZIN, YAKOV, et al., "Activation Energy of Traps in the ONO Stack of microFLASH Memory Cells", 2 pages		
HN		SAMANTA, PIYAS, et al., "Coupled charge trapping dynamics in thin SiO ₂ gate oxide under Fowler-Nordheim stress at low electron fluence", <u>Journal of Applied Physics</u> , vol. 83, no. 5, (March 1998), 2662-2669		

EXAMINER

HIEN NGUYEN

DATE CONSIDERED

3/19/04

Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional) ² Applicant is to place a check mark here if English language Translation is attached